

IN THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Previously Present) A device manufacturing method comprising:
 - (a) providing a polished silicon substrate having a background portion and one or more target portions, said background and target portions having Si-H bonds on the surface;
 - (b) irradiating said one or more target portions using a patterned beam of radiation and in the presence of oxygen to provide a layer of silicon oxide on said target portion(s);
 - (c) reacting at least a part of said background portion with a first composition comprising one or more compounds selected from 1-alkenes and 1-alkynes;
 - (d) removing said layer of silicon oxide from said target portion(s);
 - (e) reacting one or more target portions with a further composition comprising one or more compounds selected from 1-alkenes and 1-alkynes, to covalently attach said one or more compounds to said target portion(s).
2. (Previously Presented) A method according to claim 1, wherein reacting one or more target portions comprises irradiating said one or more target portions in the presence of the further composition, using a patterned beam of radiation.
3. (Previously Presented) A method according to claim 1, further comprising repeating the reacting of one or more target portions one or more times, each repetition being carried out at one or more different target portions and in the presence of a further composition comprising one or more compounds selected from 1-alkenes and 1-alkynes, each further composition being the same or different.

4. (Previously Presented) A device manufacturing method comprising:

(a1) providing a polished silicon substrate having a background portion and one or more target portions, said background and target portions having Si-H bonds on the surface;

(b1) reacting one or more target portions with a composition comprising one or more compounds selected from 1-alkenes and 1-alkynes, to covalently attach said one or more compounds to said target portion(s); and

(c1) subsequent to reacting the one or more target portions, reacting at least a part of said background portion with a first composition comprising one or more compounds selected from 1-alkenes and 1- alkynes.

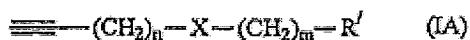
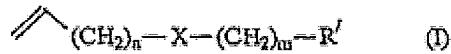
5. (Previously Presented) A method according to claim 4, wherein reacting one or more target portions comprises irradiating said one or more target portions in the presence of the composition, using a patterned beam of radiation.

6. (Previously Presented) A method according to claim 4, further comprising repeating the reacting of one or more target portions one or more times, each repetition being carried out at one or more different target portions and in the presence of the composition or a further composition, the further composition comprising one or more compounds selected from 1-alkenes and 1-alkynes, each further composition being the same or different.

7. (Previously Presented) A method according to claim 1, wherein one or more of the target portions has in its surface a part of a transistor structure.

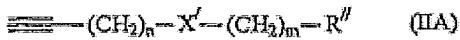
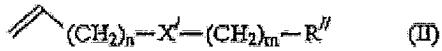
8. (Original) A method according to claim 7, wherein said silicon substrate comprises 10 or more target portions, each having a part of a transistor structure in its surface.

9. (Previously Presented) A method according to claim 1, wherein said first composition comprises one or more compounds of formula (I) or (IA):



wherein n and m independently represent an integer of from 1 to 36; X represents a single bond, -O-, -S-, -C(O)-O-, -O-C(O)- or an unsubstituted C2-C4 alkenylene or alkynylene group containing one or two double and/or triple bonds; and R' represents hydrogen.

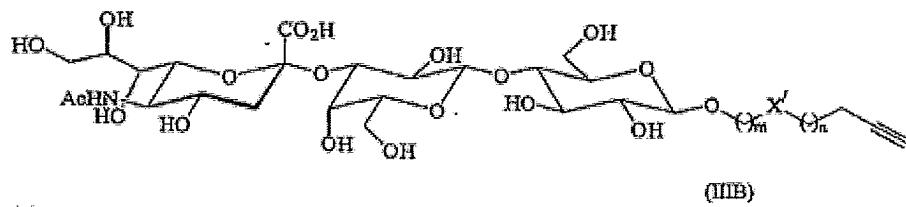
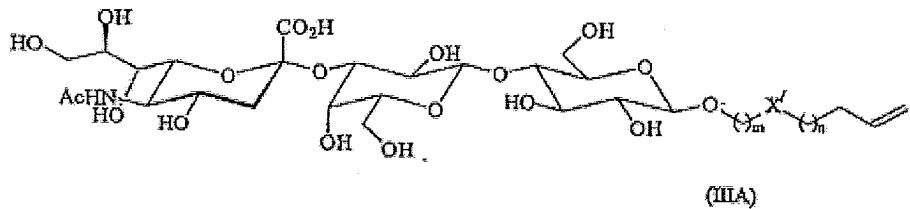
10. (Previously Presented) A method according to claim 1, wherein the further composition comprises one or more compounds of formula (II) or (IIA):



wherein n and m independently represent an integer of from 1 to 36; X' represents a single bond, -O-, -S-, -C(O)-O-, -O-C(O)- or an unsubstituted C2-C4 alkenylene or alkynylene group containing one or two double and/or triple bonds; R'' represents hydrogen or a group selected from halogens, cyanide groups, carboxylic acid derivatives including esters and amides, alkoxy groups, thio groups, amines, including mono-and di-alkylamines, hydroxy groups and receptor derivatives which are capable of interacting with a chemical or biological substance.

11. (Original) A method according to claim 10, wherein R'' represents an oligosaccharide or an oligopeptide which is capable of interacting with a chemical or biological substance.

12. (Original) A method according to claim 11, wherein said further composition comprises a compound of formula (IIIA) or(IIIB):



which is optionally protected on the saccharide units with protecting groups, wherein n, m and X' are as defined in claim 10.

13. (Previously Presented) A device obtained or obtainable by the method of claim 1.

14. – 20. (Cancelled)